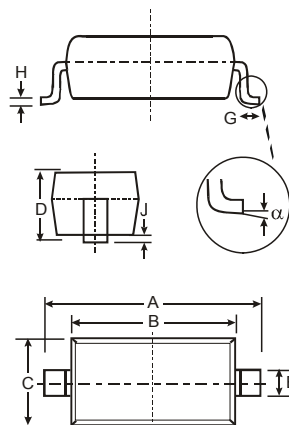


Features

- Total power dissipation: Max. 500 mW.
- Low Zener Impedance.
- High Stability and High Reliability.



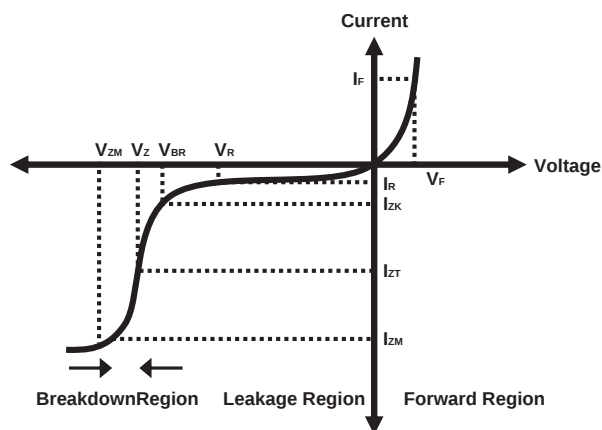
SOD-123		
Dim	Min	Max
A	3.55	3.85
B	2.55	2.85
C	1.40	1.70
D	—	1.35
E	0.45	0.65
	0.55 Typical	
G	0.25	—
H	0.11 Typical	
J	—	0.10
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 65 to + 150	$^\circ\text{C}$
Thermal Resistance Junction to Ambient Air	$R_{\theta\text{JA}}$	400	$^\circ\text{C/W}$
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.9	V

- 1) Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm²
- 2) Short duration test pulse used to minimize self-heating effect
- 3) f=1KHz

Zener I vs. V Characteristics



- V_{BR} : Voltage at I_{ZK}
- I_{ZK} : Test current for voltage V_{BR}
- Z_{ZK} : Dynamic impedance at I_{ZK}
- I_{ZT} : Test current for voltage V_Z
- V_Z : Voltage at current I_{ZT}
- Z_{ZT} : Dynamic impedance at I_{ZT}
- I_{ZM} : Maximum steady state current
- V_{ZM} : Voltage at I_{ZM}

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Device	Marking	Zener Voltage Range				Maximum Zener Impedance ³⁾			Maximum Reverse Current		Typical Temperature coefficient @ IZTC=mV/°C		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR			
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	μA	V	Min	Max	mA
BZT52C2V0	WY	2.0	1.80	2.15	5	150	600	1.0	100	1.0	-3.5	0	5
BZT52C2V4	WX	2.4	2.2	2.6	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52C2V7	W1	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52C3V0	W2	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52C3V3	W3	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52C3V6	W4	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52C3V9	W5	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V3	W6	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V7	W7	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52C5V1	W8	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52C5V6	W9	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2.0	2.5	5
BZT52C6V2	WA	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52C6V8	WB	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52C7V5	WC	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52C8V2	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52C9V1	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52C10	WF	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52C11	WG	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52C12	WH	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52C13	WI	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52C15	WJ	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52C16	WK	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52C18	WL	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52C20	WM	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52C22	WN	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52C24	WO	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52C27	WP	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52C30	WQ	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52C33	WR	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52C36	WS	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52C39	WT	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52C43	WU	43	40.0	46.0	2	100	700	1.0	0.1	32.0	10.0	12.0	5
BZT52C47	WV	47	44.0	50.0	2	100	750	1.0	0.1	35.0	10.0	12.0	5
BZT52C51	WW	51	48.0	54.0	2	125	750	1.0	0.1	38.0	10.0	12.0	5
BZT52C56	XW	56	52.0	60.0	2	135	700	1.0	0.1	39.0	10.0	12.0	5
BZT52C62	6E	62	58.0	66.0	2	200	1000	1.0	0.2	47.0	10.0	12.0	5
BZT52C68	6F	68	64.0	72.0	2	250	1000	1.0	0.2	52.0	10.0	12.0	5
BZT52C75	6H	75	70.0	79.0	2	300	1000	1.0	0.2	57	10.0	12.0	5

TYPICAL TRANSIENT CHARACTERISTICS

FIG 1 Typical Forward Characteristics

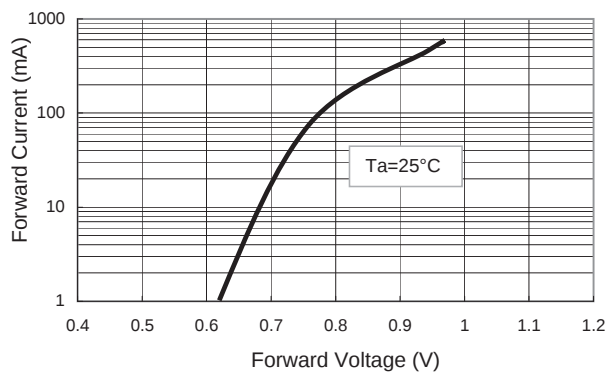


FIG 2 Zener Breakdown Characteristics

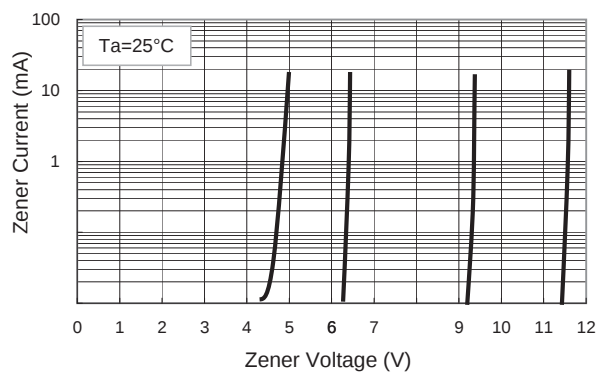


FIG 3 Zener Breakdown Characteristics

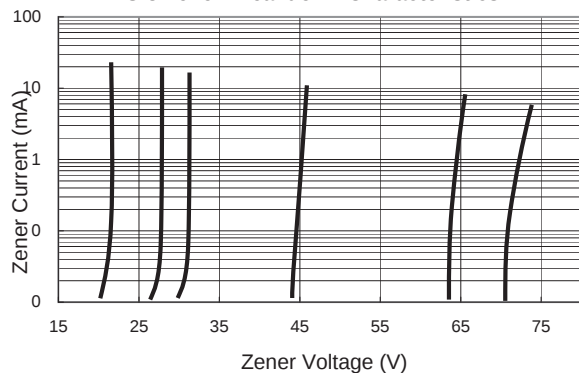


FIG 4 Admissible Power Dissipation Curve

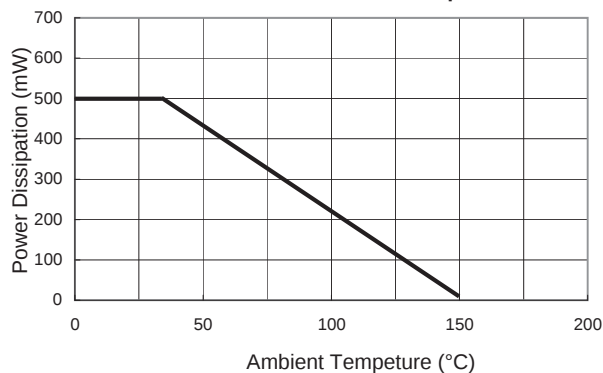


FIG 5 Typical Capacitance

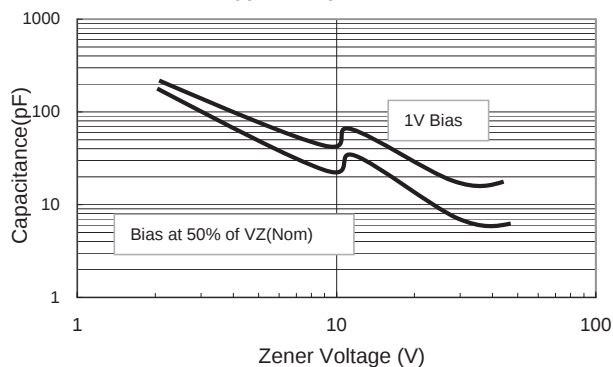
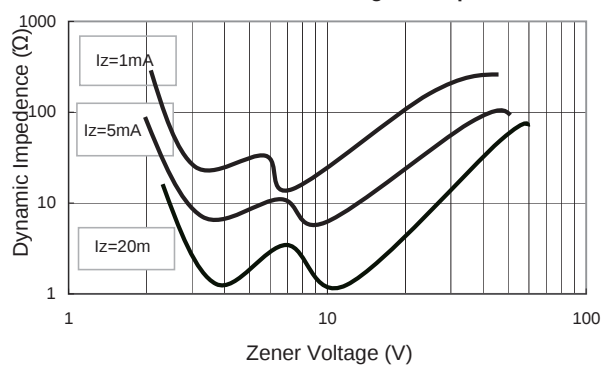


FIG 6 Effect of Zener Voltage on Impedance



IMPORTANT NOTICE

HC-SEMI reserves the right to make changes without further notice to any products herein.

HC-SEMI makes no warranty, representation or guarantee regarding

The suitability of its products for any particular purpose, nor does HC-SEMI assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages.

“Typical” parameters can and do vary in different applications. All operating parameters, including “Typicals” must be validated for each customer application by customer’s technical experts.

HC-SEMI products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the HC-SEMI product could create a situation where personal injury or death may occur.

Should Buyer purchase or use HC-SEMI products for any such unintended or unauthorized application, Buyer shall indemnify and hold HC-SEMI and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that HC-SEMI was negligent regarding the design or manufacture of the part.